NJL5162K/64K/66K/68K

# PHOTO REFLECTOR

## GENERAL DESCRIPTION

The NJL5162K/5164K/5166K/5168K are super miniature and super thin photo reflector; which consist of high output infrared emitting and high sensitve Si photo dralington transistor.

#### FEATURES

JRC

- Super miniature, super thin type
- Built-in visible light cut-off filter.
- High output, high S/N ratio.

#### APPLICATIONS

- End detector of video, audio tape.
- Rotation detection and control of various motors, audio turn-tables.
- Paper edge detection of facsimile printer, X-Y recorder, so on.
- Reading out the charactors of bar code reader, encorder and the automatic vending machine etc.
- Various detection of industrial system, such as FDD, Robot.

## ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Emitter			
Forward Current (Continuous)	l <sub>F</sub>	50	mA
Pulse Forward Current	IFP	500(note 1)	mA
Reverse Voltage (Continuous)	VR	6	V
Power Dissipation	PD	75	mW
Detector			
Collector-Emitter Voltage	VCEO	25	v
Emitter-Collector Voltage	VECO	6	v
Collector Current	Ic	20	mA
Collector Power Dissipation	Pc	75	mW
Coupled			
Total Power Dissipation	Ptot	100	mW
Operating Temperature	Topr	$-20 \sim +90$	°C
Storage Temperature	Tstg	$-30 \sim +100$	°C
Soldering Temperature	T <sub>sol</sub>	260	°C
		(10sec. 1.5mm from body)	

(note 1): Pulsewidth  $\leq 10\mu$ s. Duty Ratio 0.01

#### ■ ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

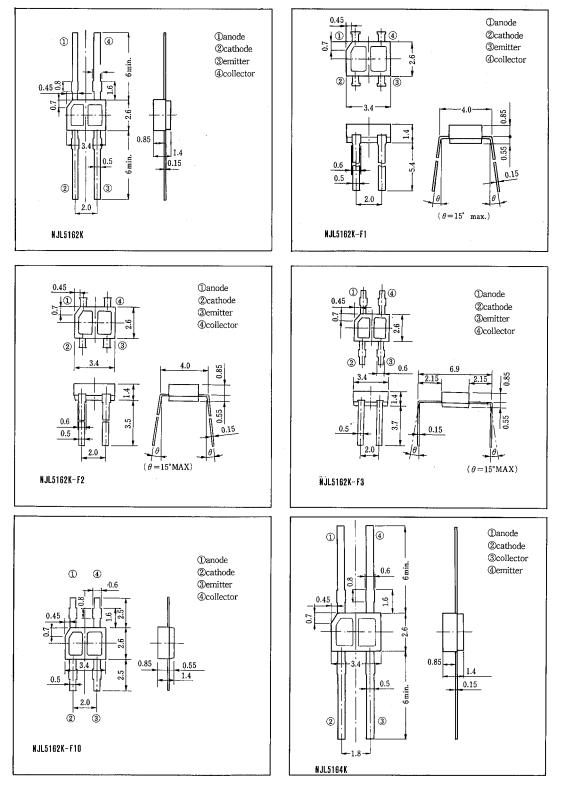
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Emitter						
Forward Voltage	V <sub>F</sub>	$I_F = 4mA$		_	1.2	v
Reverse Current	I <sub>R</sub> .	$V_R = 6V$	—		1	μA
Capacitance	Ct	$V_R = 0V, f = 1MHz$	_	25	_	pF
Detector					}	
Dark Current	I <sub>CEO</sub>	$V_{CE} = 20V$		_	1	μA
Collector-Emitter Voltage	VCEO	$I_{\rm C} = 100 \mu \rm A$	25	_		v
Emitter-Collector Current	I <sub>ECO</sub>	V <sub>ECO</sub> =6V	_	_	100	μA
Coupled						
Output Current	Io	$I_{F} = 4mA$ , $V_{CE} = 2V$ , $d = 0.7mm$	0.6	3	16	mA
Operating Dark Current	<b>I</b> CEOD	$I_F = 4mA$ , $V_{CE} = 2V$		_	1	μA
Rise Time	tr	$I_0 = 10mA$ , $V_{CE} = 2V$ , $R_L = 100Q$ , $d = 0.7mm$	_	100		μs
Fall Time	tſ	$I_0 = 10mA$ , $V_{CE} = 2V$ , $R_L = 100\Omega$ , $ d  = 0.7mm$	-	70		μs

#### RANK OF OUTPUT CURRENT

RANK	А	В	С
I <sub>O</sub> (mA)	4~16	1.6~6	0.6~2.1

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# ■ OUTLINE (typ.) Unit: mm

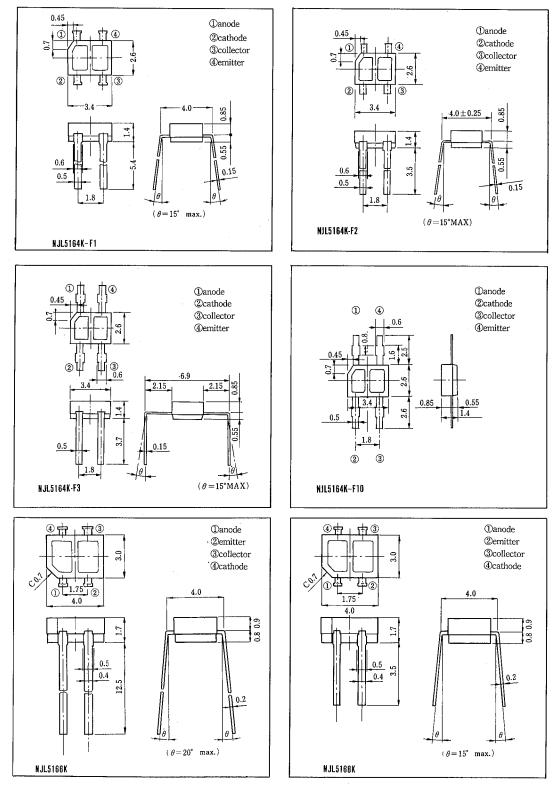


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OUTLINE (typ.) Unit: mm

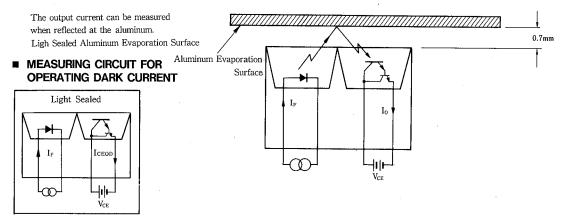


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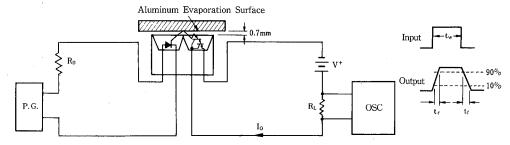
2-20

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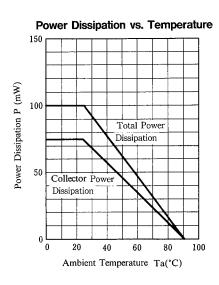
# ■ MEASURING SPECIFICATION FOR OUTPUT CURRENT



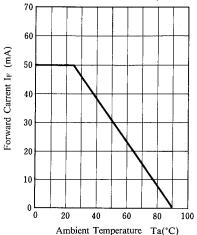
## ■ MEASURING CIRCUIT FOR RESPONSE TIME



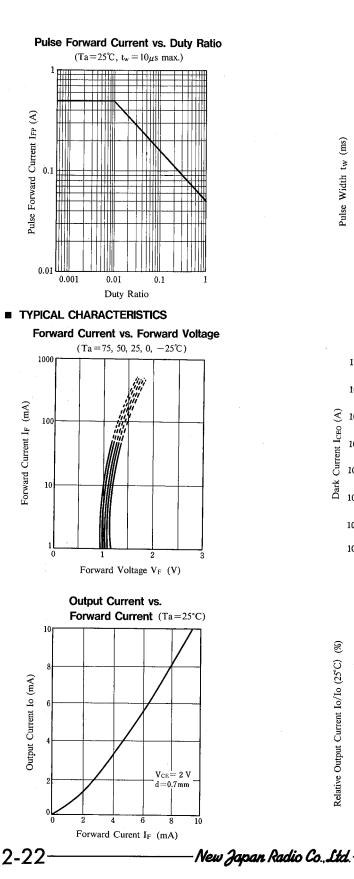
# ■ MAXIMUM RATING CURVES

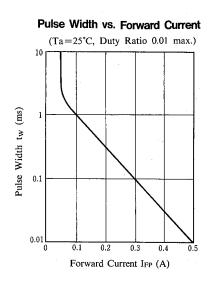


## Forward Current vs. Temperature

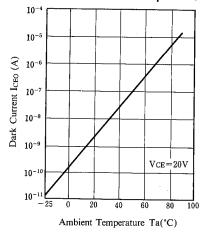


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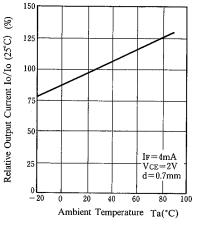




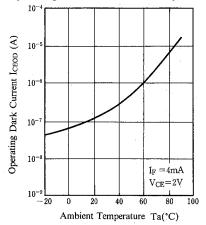
Dark Current vs. Temperature

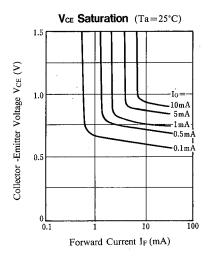


Output Current vs. Temperature

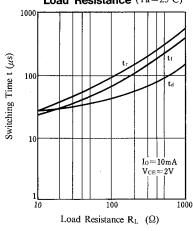


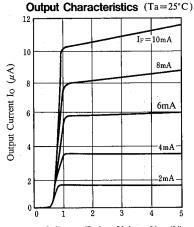
**Operating Dark Current vs. Temperature** 





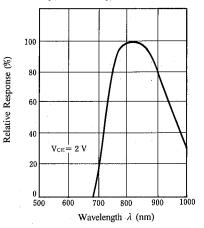
Switching Time vs. Load Resistance (Ta=25°C)



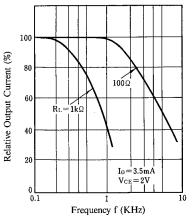


Collector -Emitter Voltage V<sub>CE</sub> (V)

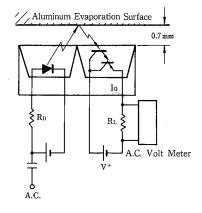
Spectral Response (Ta=25°C)



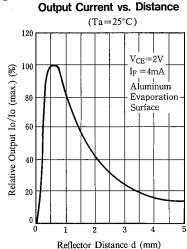
Output Current vs. Frequency (Ta=25°C)

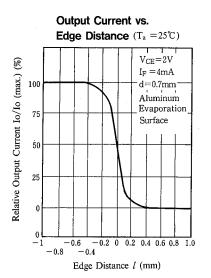


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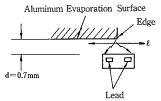


# ■ MEASURING CIRCUIT FOR FREQUENCY CHARACTERISTICS





MEASURING SPECIFICATION FOR EDGE RESPONSE



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# PRECAUTION FOR HANDLING

#### 1. Soldering

- 1) Avoid the reflow method and the solder to touch the body of the device during wave soldering. This is to prevent changes in optical characteristics of the device.
- 2) Recommended in Soldering

260℃ maximum

- Temperature Time Lead
- Soldering Position
- less than 10 seconds At least 1.5mm from body
- 3) Soldering is recommended to be done in as short period of the time as possible by controlling the temperature of the soldering iron or by the iron of less than 15 watts.
- 4) The resin gets softened right after soldered, so, the following care has to be taken.
  - Not to contact the lens surface to anything
  - Not to dip the device into water or any solvents
- 5) It is recommended not to solder when the leads or between the lead get pulled, depressed or twisted.
- 6) In the case of using rosin flux, be careful to avoid contact with the lens surface. If the lens is covered with the flux, the specified characteristics cannot be achieved.

#### 2. Post Solder Cleaning

- 1) Organic solvents for flux removal like trichloroethlene, acetone, thinner etc, might attack the lens surface. It is preferable to use less reactive solvents, Methyl Alcohol, Isopropyle Alcohol.
- 2) Cleaning Operation
  - Cleaning Solvent Temperature : 35°C maximum Dipping Time : 3 minute maximum

#### 3. Attention in handling

- 1) Treat not to touch the lens surface.
- 2) Avoid dust and any other foreign materials(flux, paint, bonding material, etc)on the lens surface.
- Never to apply reverse voltage(V<sub>EC</sub>) of more than 6V on the photo transistor when measuring the characteristics or adjusting the system. If applied, it causes to lower the sensitivity.
- 4) When mounting, special care has to be taken on the mounting position and tilting of the device because it is very important to place the device to the optimum position to the object.

#### 4. Storage

The leads are silver plated and they are discolored if the device is left open to the air for long after taken out of the envelope. It causes deterioration of soldering characteristics. Mount the device as short as possible after opening the envelope.

# **MEMO**

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